

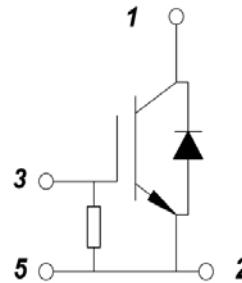
PRODUCT FEATURES

- High short circuit capability, self limiting short circuit current
- IGBT CHIP(T4 Fast Trench+Field Stop technology)
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Low switching losses
- 5K Ω Gate Protected Resistance Inside



APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems



IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{CES}	Collector Emitter Voltage	$T_J=25^\circ\text{C}$	1200	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^\circ\text{C}$	1050	A
		$T_C=75^\circ\text{C}$	800	
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	1600	
P_{tot}	Power Dissipation Per IGBT		3950	W

Reverse-Diode

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^\circ\text{C}$	1200	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^\circ\text{C}$	800	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	1600	
I^2t		$T_J=125^\circ\text{C}$, $t=10\text{ms}$, $V_R=0\text{V}$	51200	A^2S

IGBT-inverter

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=32\text{mA}$	5.4	6.0	6.5		
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=800\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		2.1	2.5	V	
		$I_C=800\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.5			
I_{CES}	Collector Leakage Current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA	
		$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$			10	mA	
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=125^\circ\text{C}$	-400		400	nA	
R_{gint}	Integrated Gate Resistor			1		Ω	
Q_g	Gate Charge	$V_{CE}=600\text{V}, I_C=800\text{A}, V_{GE}=15\text{V}$		3.8		μC	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		50		nF	
C_{res}	Reverse Transfer Capacitance				2.8		nF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=600\text{V}, I_C=800\text{A}$ $R_G=1.0\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		250		ns
			$T_J=125^\circ\text{C}$		320		ns
			$T_J=150^\circ\text{C}$		340		ns
t_r	Rise Time		$T_J=25^\circ\text{C}$		90		ns
			$T_J=125^\circ\text{C}$		95		ns
			$T_J=150^\circ\text{C}$		100		ns
$t_{d(off)}$	Turn off Delay Time	$T_J=25^\circ\text{C}$		550		ns	
		$T_J=125^\circ\text{C}$		650		ns	
		$T_J=150^\circ\text{C}$		700		ns	
t_f	Fall Time	$T_J=25^\circ\text{C}$		60		ns	
		$T_J=125^\circ\text{C}$		80		ns	
		$T_J=150^\circ\text{C}$		90		ns	
E_{on}	Turn on Energy	$V_{CC}=600\text{V}, I_C=800\text{A}$ $R_G=1.0\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=125^\circ\text{C}$		65		mJ
			$T_J=150^\circ\text{C}$		70		mJ
E_{off}	Turn off Energy		$T_J=125^\circ\text{C}$		50		mJ
			$T_J=150^\circ\text{C}$		55		mJ
I_{sc}	Short Circuit Current		$t_{psc}\leq 10\mu\text{s}, V_{GE}=15\text{V}$ $T_J=125^\circ\text{C}, V_{CC}=600\text{V}$		3200		A
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.038	K/W	

Reverse-Diode

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t
V_F	Forward Voltage	$I_F=800\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		2.25	2.6	V
		$I_F=800\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		2.25		
t_{rr}	Reverse Recovery Time	$I_F=800\text{A}, V_R=600\text{V}$		450		ns
I_{RRM}	Max. Reverse Recovery Current	$dI_F/dt=-8000\text{A}/\mu\text{s}$		720		A
Q_{RR}	Reverse Recovery Charge	$T_J=125^\circ\text{C}$		95		μC
E_{rec}	Reverse Recovery Energy			40		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.065	K/W

MODULE CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise sp

Symbol	Parameter/Test Conditions		Values	t
T_{Jmax}	Max. Junction Temperature		175	°C
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M6)	2.5~5	Nm
	to terminal	Recommended (M4)	0.7~1.1	Nm
Weight			330	g

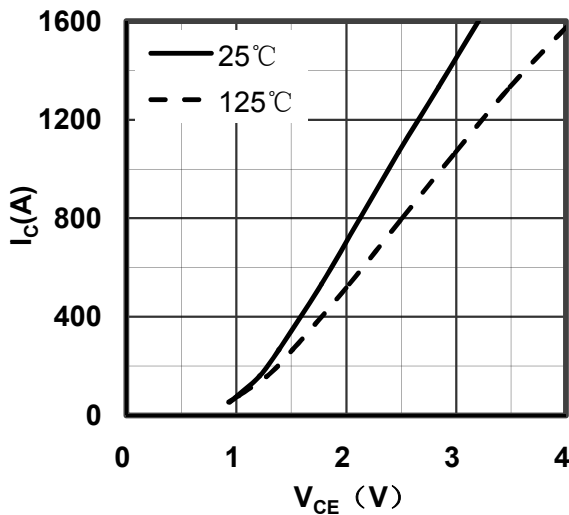


Figure 1. Typical Output Characteristics IGBT-inverter

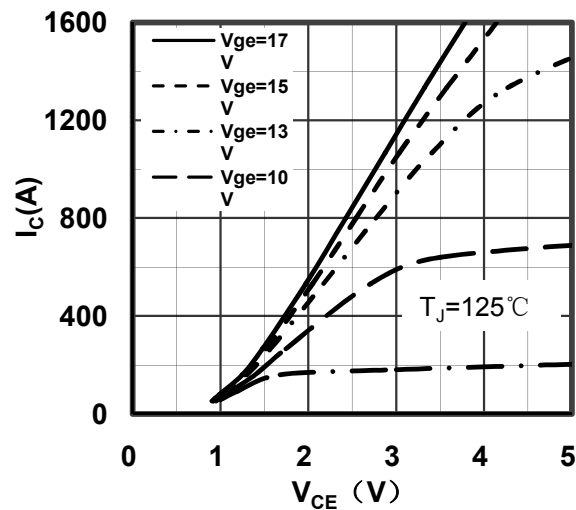


Figure 2. Typical Output Characteristics IGBT-inverter

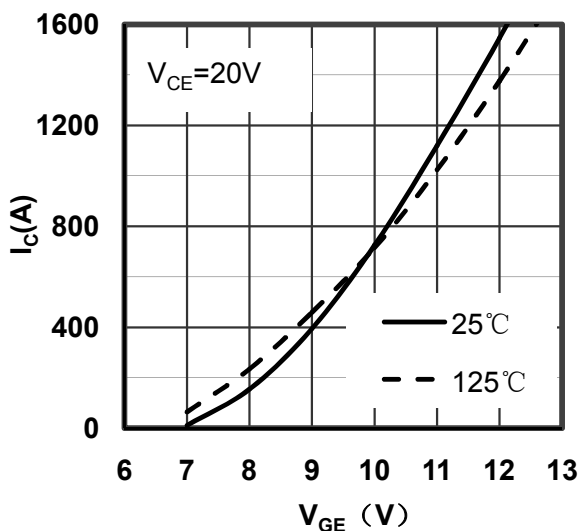


Figure 3. Typical Transfer Characteristics IGBT-inverter

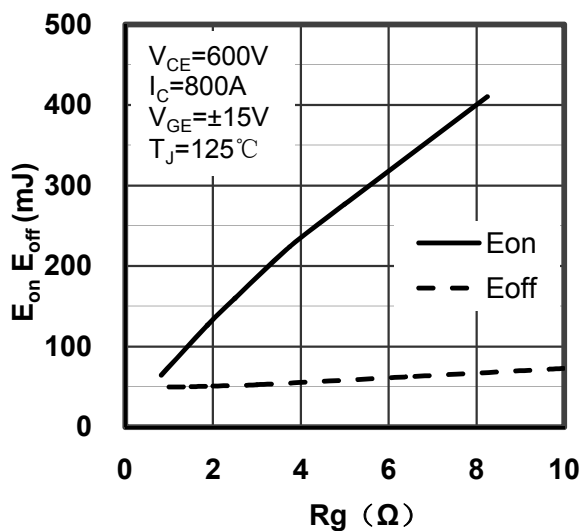


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

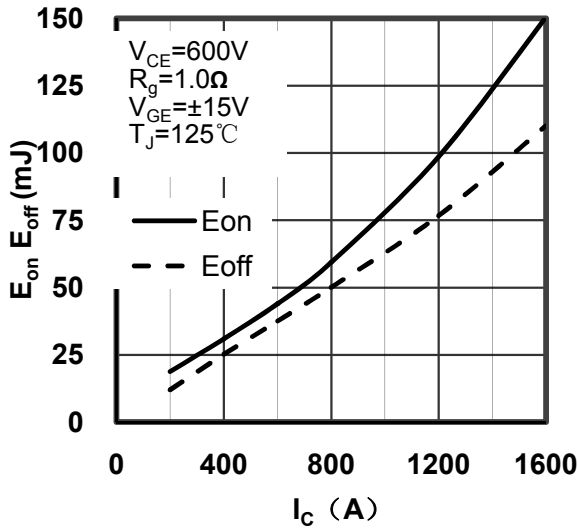


Figure 5. Switching Energy vs Collector Current IGBT-inverter

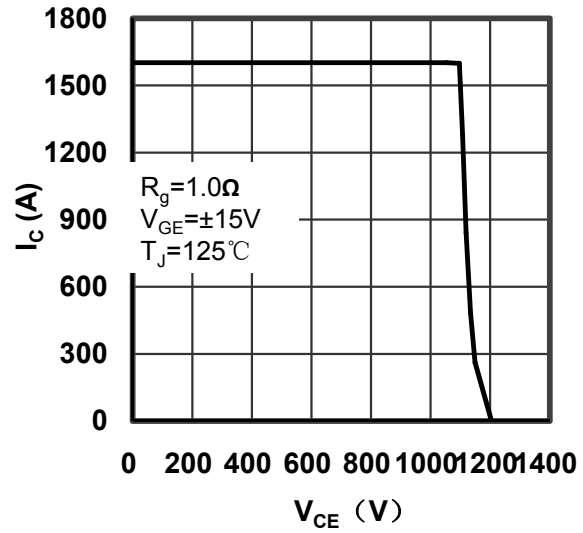


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

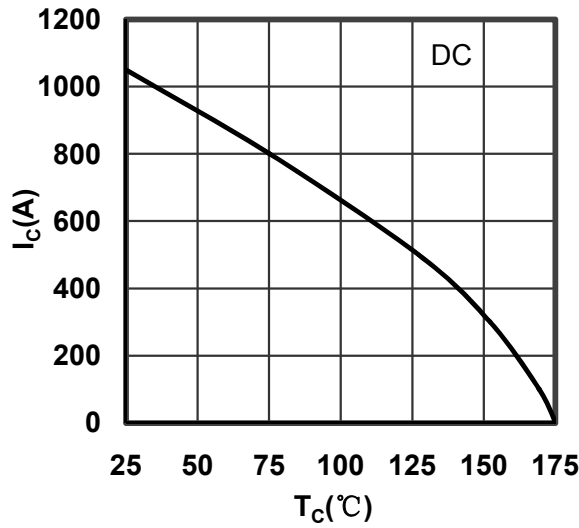


Figure 7. Collector Current vs Case temperature IGBT-inverter

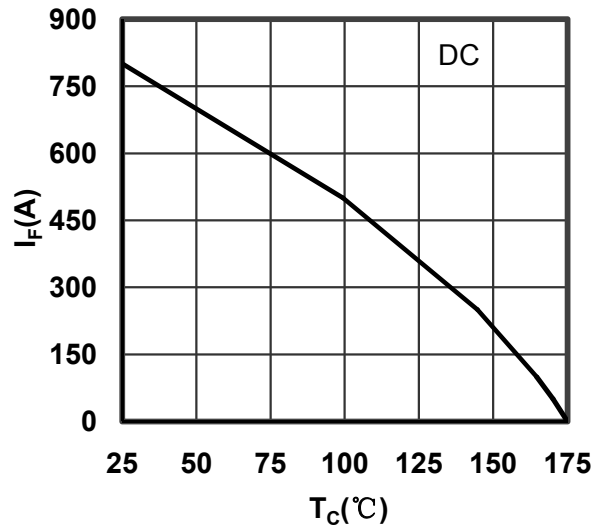


Figure 8. Forward current vs Case temperature

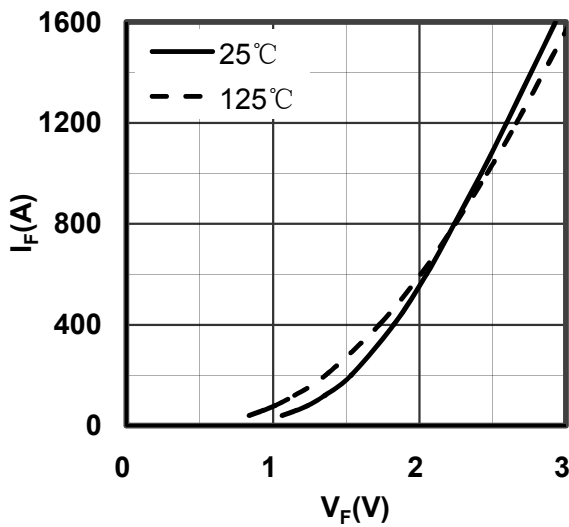


Figure 9. Diode Forward Characteristics Reverse-Diode

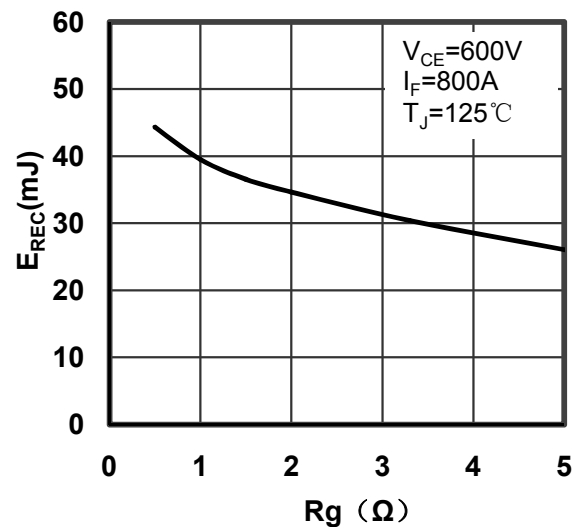


Figure 10. Switching Energy vs Gate Resistor Reverse-Diode

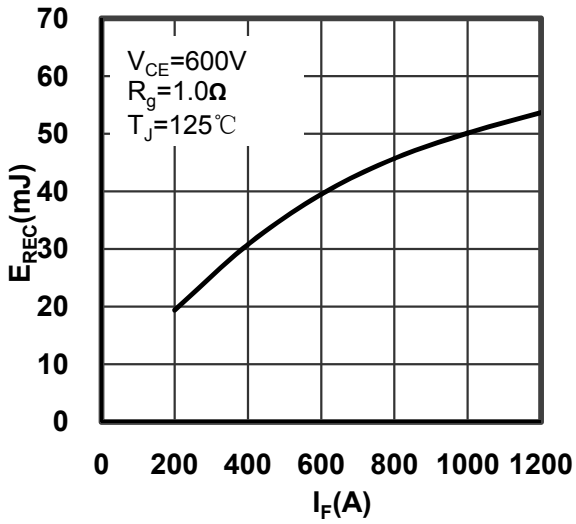


Figure 11. Switching Energy vs Forward Current Reverse-Diode

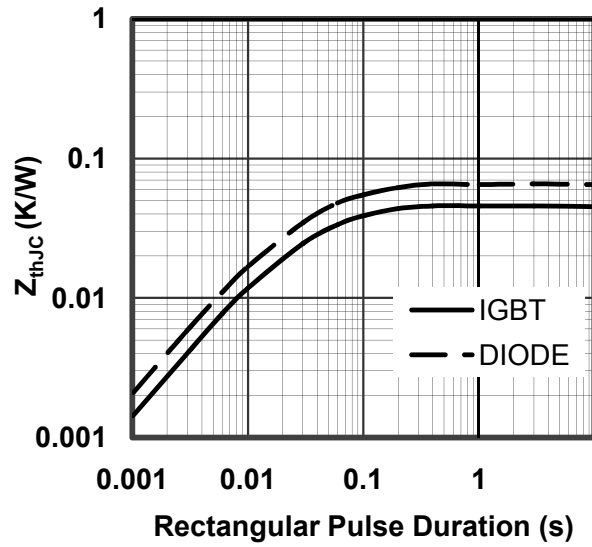
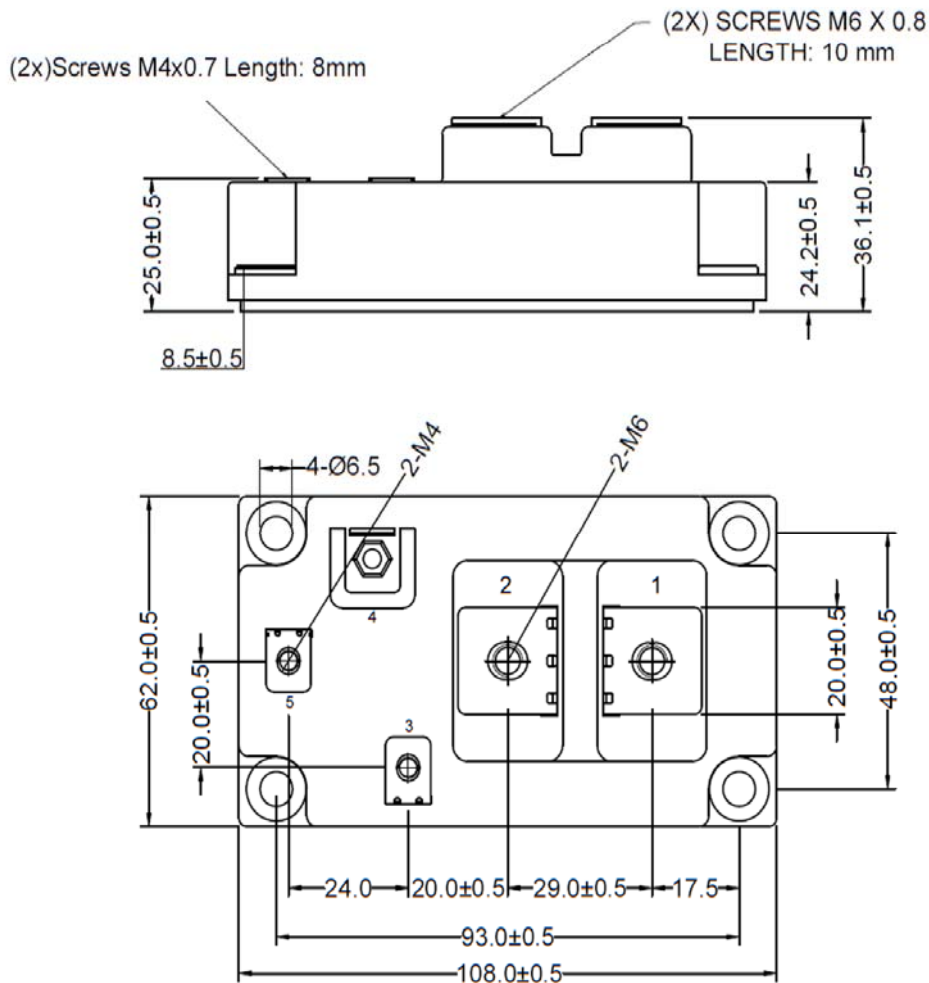


Figure 12. Transient Thermal Impedance of Reverse-Diode and IGBT-inverter



Dimensions in (mm)
Figure 13. Package Outline